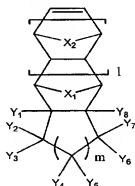


ABSTRACT OF THE DISCLOSURE

Photoresist monomers of following Formula 1, photoresist polymers thereof, and photoresist compositions containing the same. The photoresist composition has excellent etching resistance, heat resistance and adhesiveness to a wafer, and is developable in aqueous tetramethylammonium hydroxide (TMAH) solution. In addition, the photoresist composition has low light absorbance at 157nm wavelength, and thus is suitable for a photolithography process using ultraviolet light sources such as VUV (157nm) in fabricating a minute circuit for a high integration semiconductor device.

Formula 1



wherein, X₁, X₂, Y₁, Y₂, Y₃, Y₄, Y₅, Y₆, Y₇, Y₈, l and m are as defined in the specification of the invention.